

Description

The HSM8016 is the high cell density trenched N-ch MOSFETs, which provide excellent R_{DS(ON)} and gate charge for most of the synchronous buck converter applications.

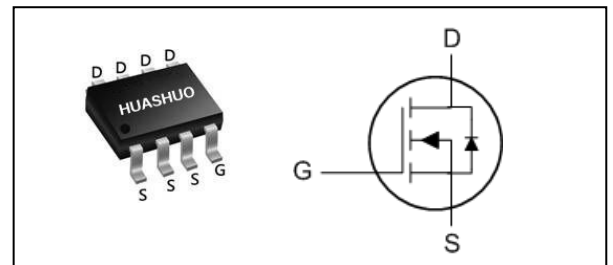
The HSM8016 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V _{DS}	80	V
R _{DS(ON),max}	12	mΩ
I _D	11	A

SOP8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	80	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Continuous Drain Current ¹	11	A
I _D @T _A =70°C	Continuous Drain Current ¹	9	A
I _{DM}	Pulsed Drain Current ²	80	A
EAS	Single Pulse Avalanche Energy ³	80	mJ
P _D @T _A =25°C	Total Power Dissipation ⁴	2.8	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹ (t ≤ 10S)	---	45	°C/W
	Thermal Resistance Junction-ambient ¹ (Steady State)	---	85	°C/W



Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	80	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=8A$	---	9.6	12	$m\Omega$
		$V_{GS}=4.5V, I_D=6A$	---	12	14.5	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=64V, V_{GS}=0V, T_J=25^\circ C$	---	---	1	μA
		$V_{DS}=64V, V_{GS}=0V, T_J=55^\circ C$	---	---	5	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=10A$	---	32	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	0.7	---	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=64V, V_{GS}=10V, I_D=4A$	---	60.9	---	nC
Q_{gs}	Gate-Source Charge		---	8.1	---	
Q_{gd}	Gate-Drain Charge		---	17.9	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=40V, V_{GS}=10V, R_G=3.3\Omega, I_D=4A$	---	12.2	---	ns
T_r	Rise Time		---	24.5	---	
$T_{d(off)}$	Turn-Off Delay Time		---	50.5	---	
T_f	Fall Time		---	17.6	---	
C_{iss}	Input Capacitance	$V_{DS}=50V, V_{GS}=0V, f=1MHz$	---	3120	---	pF
C_{oss}	Output Capacitance		---	140	---	
C_{rss}	Reverse Transfer Capacitance		---	110	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V, \text{Force Current}$	---	---	62	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=4A, dI/dt=100A/\mu s, T_J=25^\circ C$	---	18.6	---	nS
Q_{rr}	Reverse Recovery Charge		---	65	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=50V, V_{GS}=10V, L=0.1mH, I_{AS}=40A$
- 4.The power dissipation is limited by 150 $^\circ C$ junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

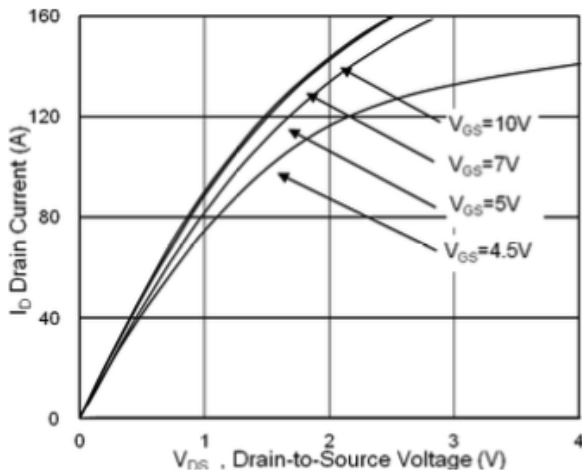


Fig.1 Typical Output Characteristics

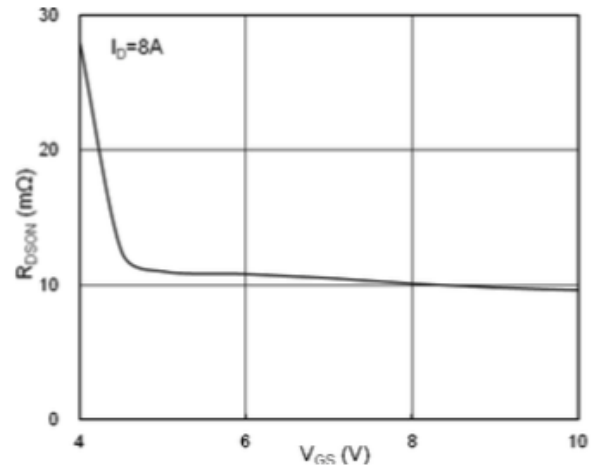


Fig.2 On-Resistance vs. Gate-Source Voltage

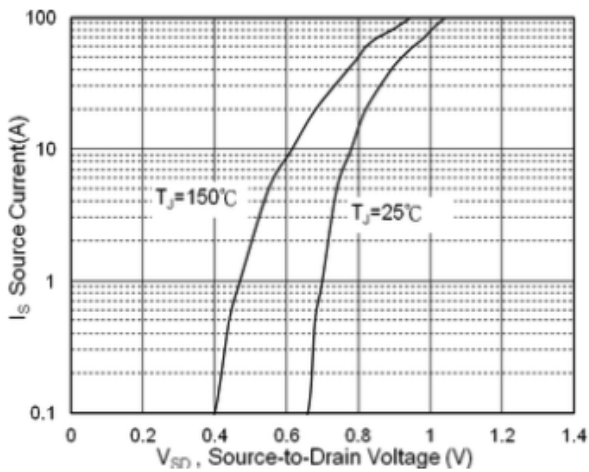


Fig.3 Forward Characteristics of Reverse

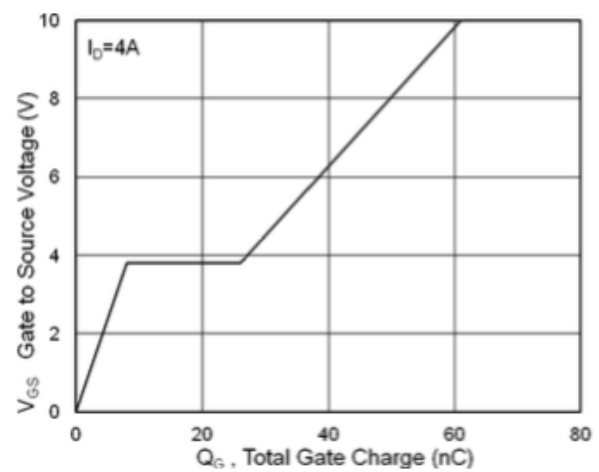


Fig.4 Gate-Charge Characteristics

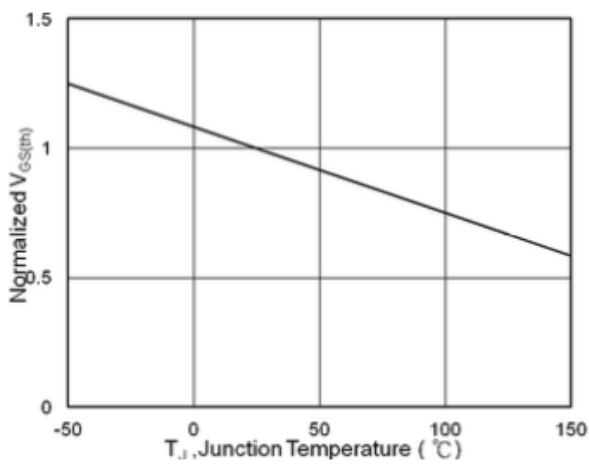


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

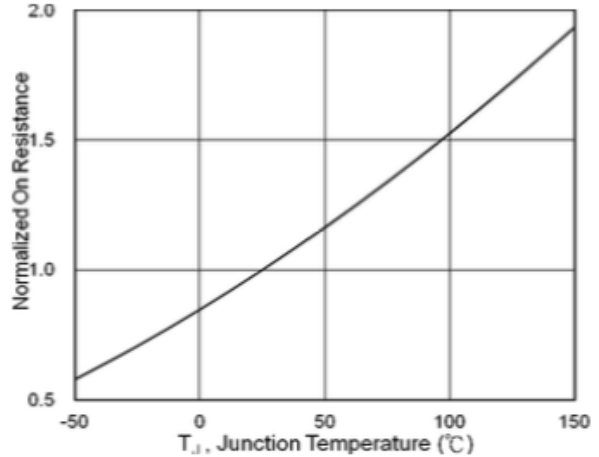


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

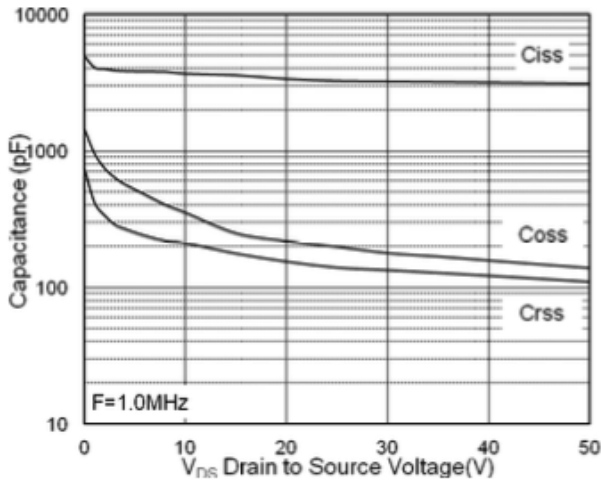


Fig.7 Capacitance

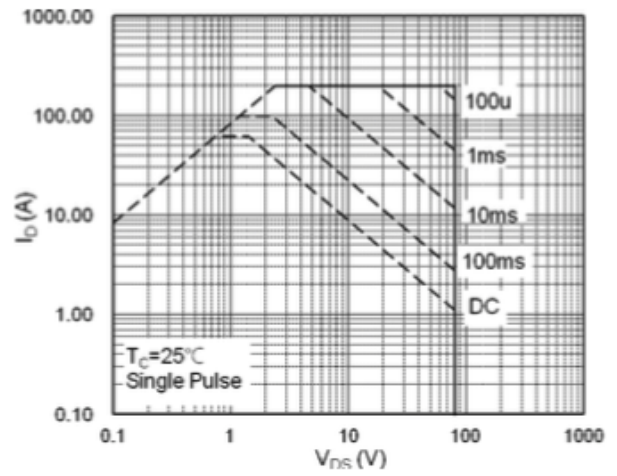


Fig.8 Safe Operating Area

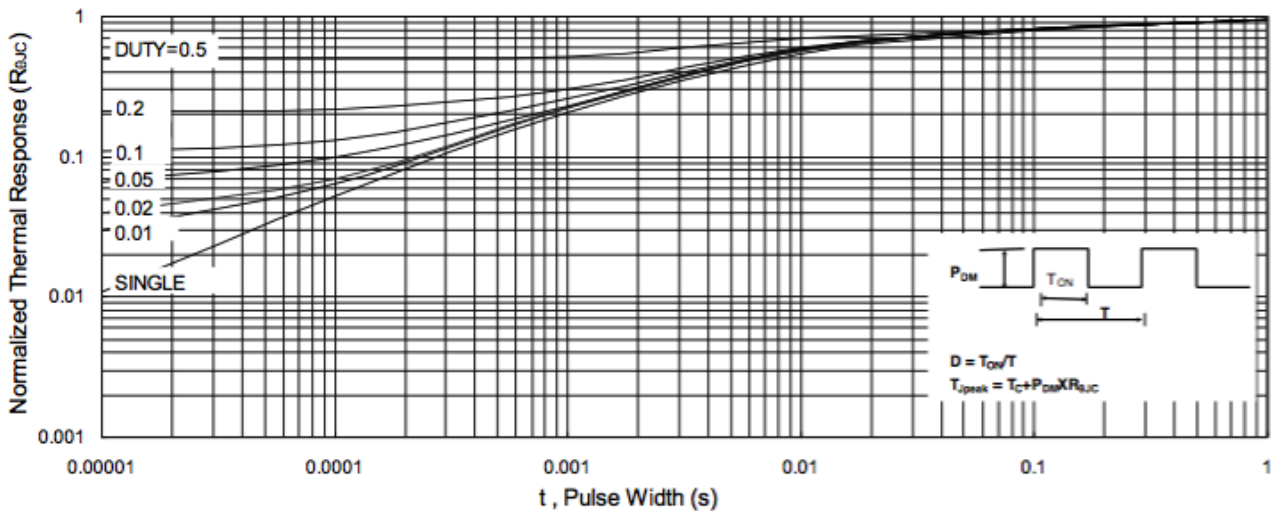


Fig.9 Normalized Maximum Transient Thermal Impedance

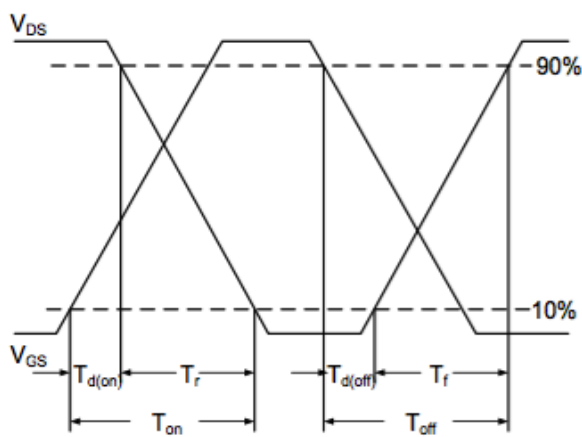


Fig.10 Switching Time Waveform

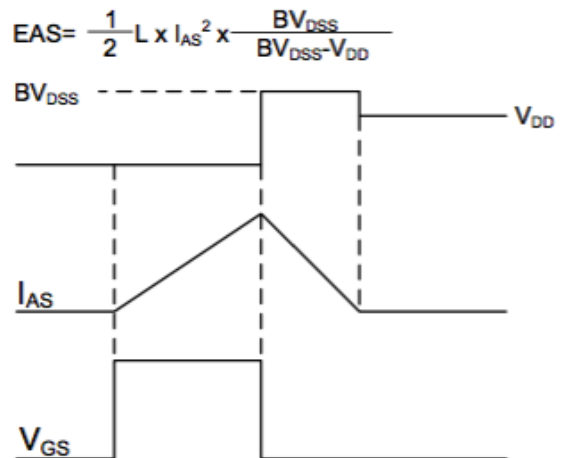


Fig.11 Unclamped Inductive Switching Waveform



Ordering Information

Part Number	Package code	Packaging
HSM8016	SOP-8	2500/Tape&Reel

